Features

- Split Gate Trench MOSFET Technology
- High Density Cell Design For Ultra Low $R_{DS(on)}$
- Moisture Sensitivity Level 1
- Halogen Free."Green"Device(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel MOSFET

Maximum Ratings

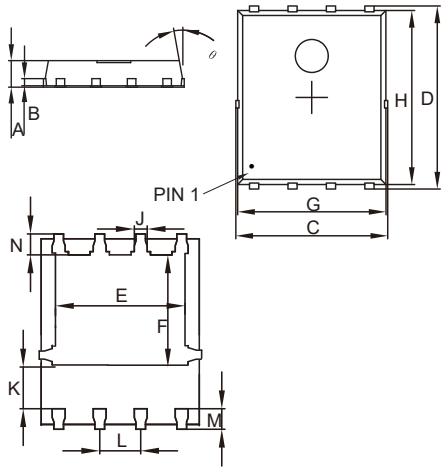
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient(1)
- Thermal Resistance: 1.2°C/W Junction to Case

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	74	A
	T_C=100°C		46	
Pulsed Drain Current(Note 3)		I_{DM}	296	A
Total Power Dissipation(Note 4)		P_D	104	W
Single Pulsed Avalanche Energy(Note 5)		E_{AS}	289	mJ

Note:

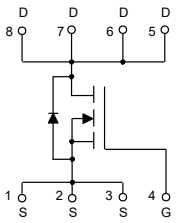
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25℃, V_{DD}=30V, V_{GS}=10V, R_G=25Ω, L=2mH.

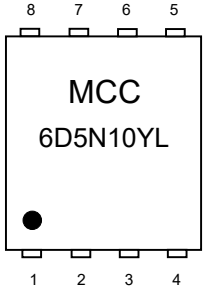
DFN5060



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.203	0.219	5.15	5.55	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Internal Structure and Marking Code





Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	100			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.1	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A		5	6.5	mΩ
		V_{GS}=4.5V, I_D=20A		6.5	8.5	
Gate Resistance	R_g	f=1 MHz, Open drain		2		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				74	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=37A			1.2	V
Reverse Recovery Time	t_{rr}	I_F=37A, dI/dt=550A/μs		34		ns
Reverse Recovery Charge	Q_{rr}			150		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V,f=100KHz		2870		pF
Output Capacitance	C_{oss}			1120		
Reverse Transfer Capacitance	C_{rss}			22		
Total Gate Charge	Q_g	V_{DS}=50V,V_{GS}=10V,I_D=37A		45		nC
Gate-Source Charge	Q_{gs}			10		
Gate-Drain Charge	Q_{gd}			9.5		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=50V, V_{GS}=10V, R_G=2.2Ω,I_D=37A		13		ns
Turn-On Rise Time	t_r			77		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			9		

Curve Characteristics

Fig.1 - Typical Output Characteristics

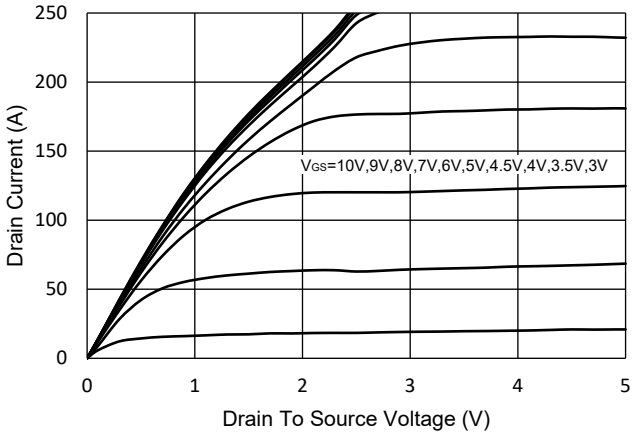


Fig.2 - Transfer Characteristics

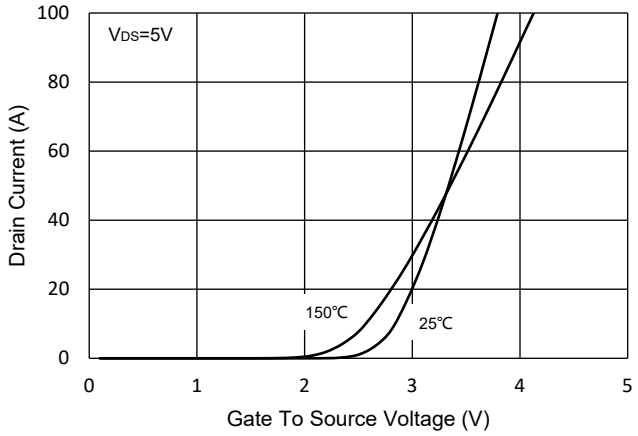


Fig.3 - $R_{DS(ON)}$ - V_{GS}

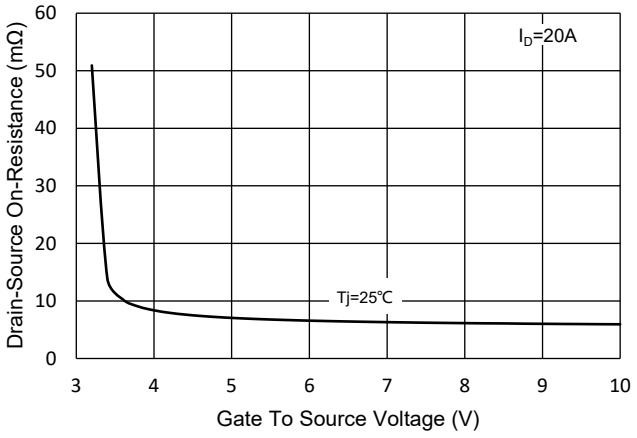


Fig.4 - $R_{DS(ON)}$ - I_D

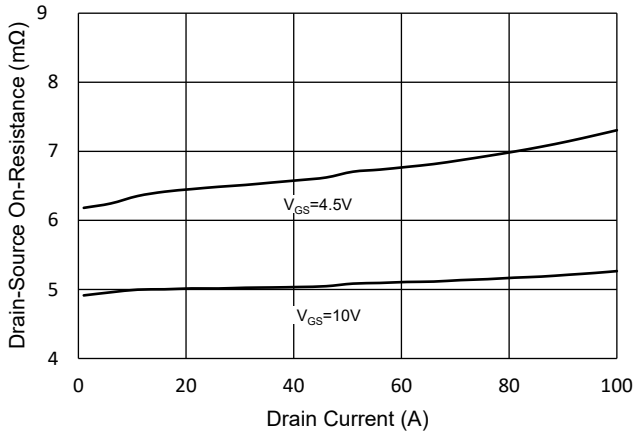


Fig. 5 - Capacitance Characteristics

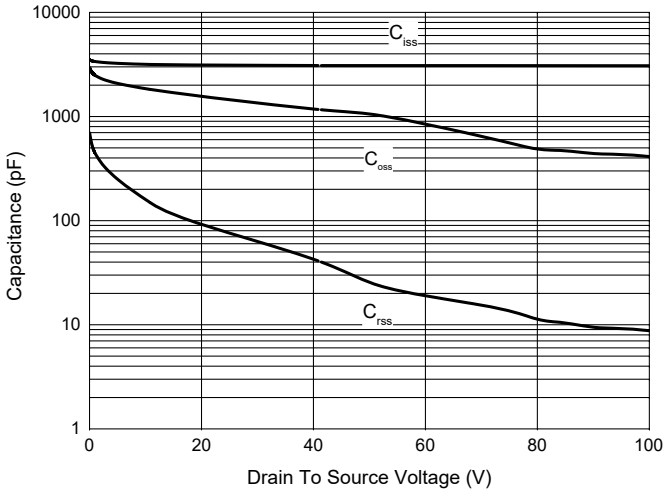
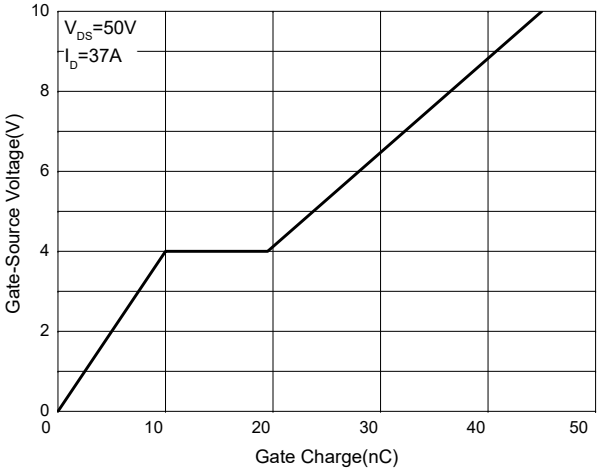


Fig. 6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

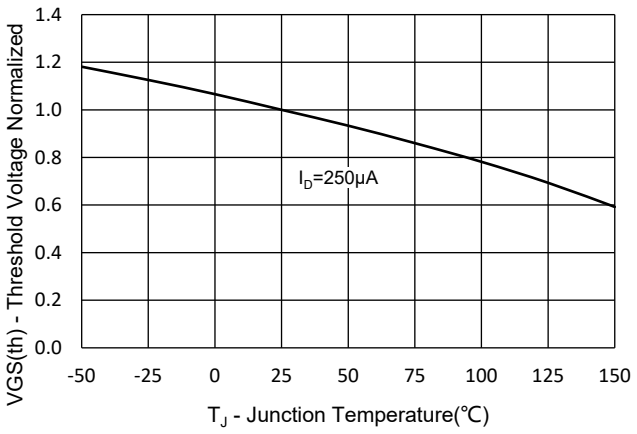


Fig.8 - Normalized On Resistance Characteristics

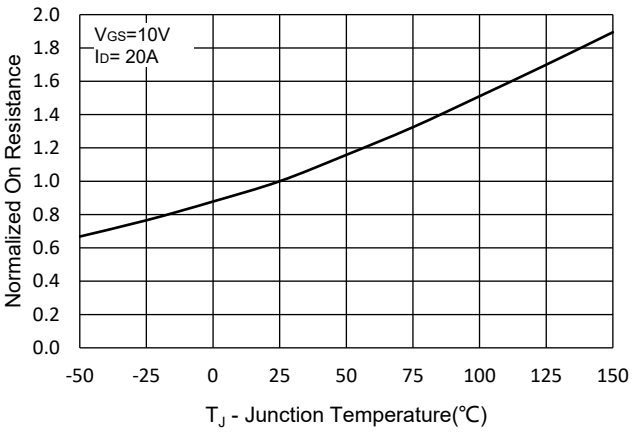


Fig.9 - I_S - V_{SD}

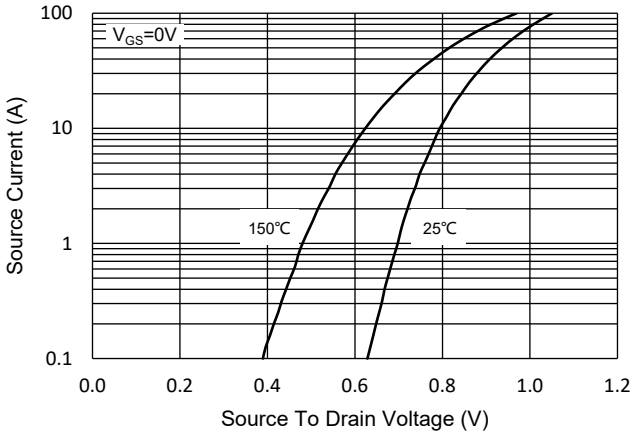


Fig.10 - Drain Current

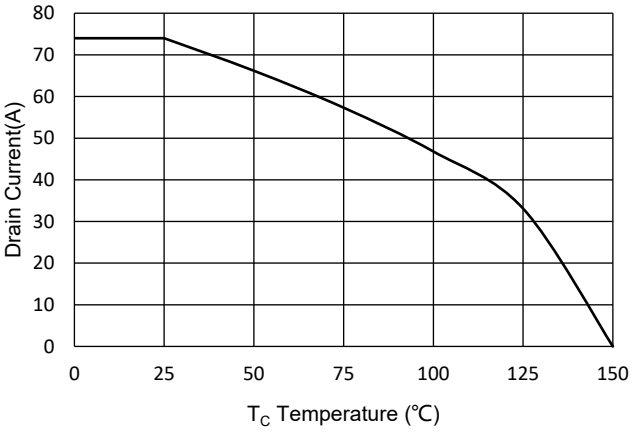
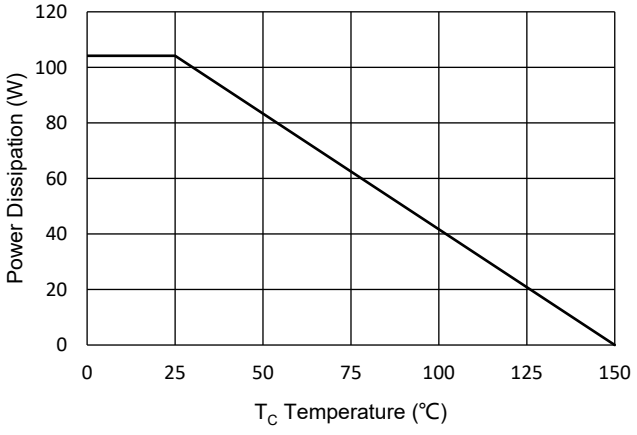


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

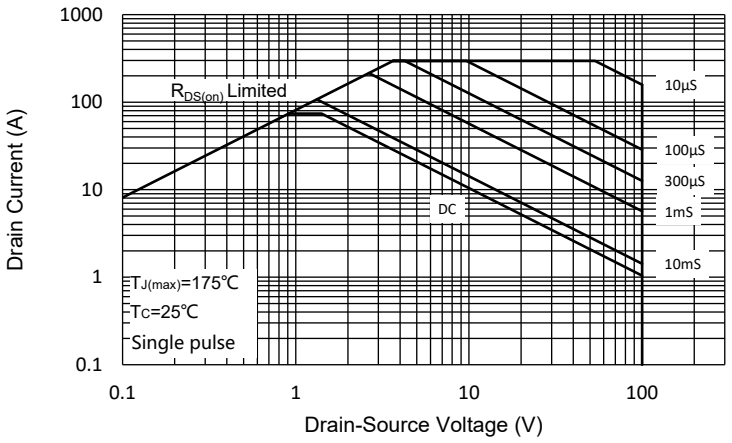
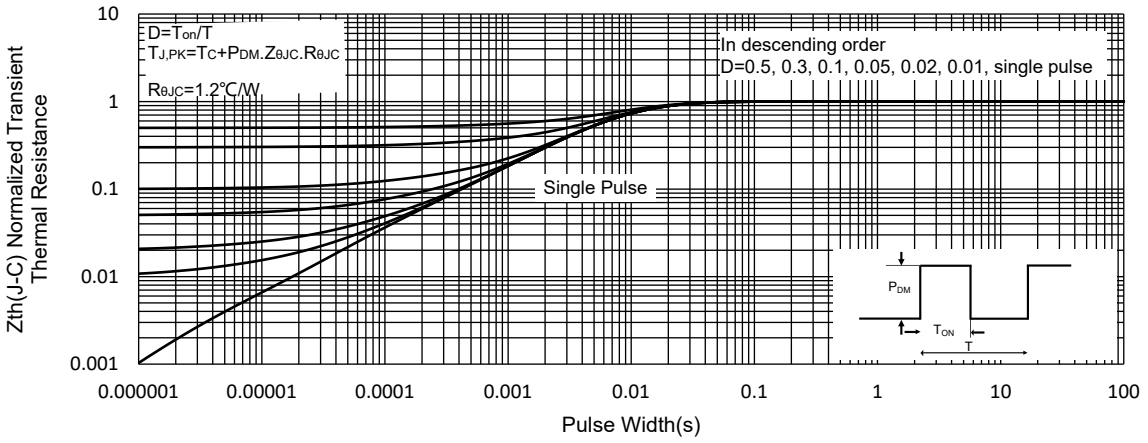


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel